

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1490** is a Common Emitter Device Designed for Class A and AB Amplifier Applications in Television Band IV & V Transmitters.

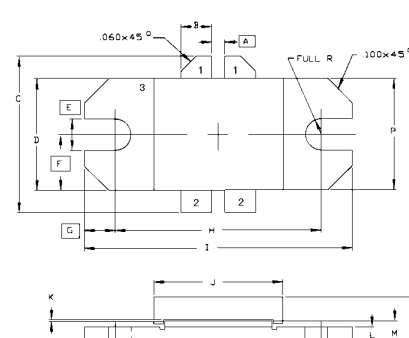
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Internal Matching

MAXIMUM RATINGS

I_C	8.0 A
V_{CB}	45 V
P_{DISS}	155 W @ $T_C = 25^\circ\text{C}$
T_J	-55°C to $+200^\circ\text{C}$
T_{STG}	-55°C to $+200^\circ\text{C}$
q_{JC}	1.15 $^\circ\text{C/W}$

PACKAGE STYLE .450 BAL FLG.(A)

		MINIMUM Inches/mm		MAXIMUM Inches/mm	
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		.055/.140		K	
B	120/3.05	.130/3.30		L	.055/.140
C		.785/19.94		M	.080/2.03
D	.455/11.56	.465/11.81		N	.095/2.41
E	.130/3.30			P	.455/11.56
F	.230/5.84				
G	.128/3.25				
H	.838/21.28	.850/21.59			
I	1.095/27.81	1.105/28.07			
J	.525/13.34	.535/13.59			

1 = Collector 2 = Base
3 = Emitter

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS (PER SIDE)			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200\text{ mA}$			30			V
BV_{CBO}	$I_C = 50\text{ mA}$			45			V
BV_{EBO}	$I_E = 10\text{ mA}$			3.0			V
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 3.0\text{ A}$		10		100	---
C_{OB}	$V_{CB} = 28\text{ V}$	$f = 1.0\text{ MHz}$			72		pF
G_P	$V_{CE} = 26.5\text{ V}$	$I_C = 2 \times 1.6\text{ A}$	$f = 860\text{ MHz}$	8.0	9.0		dB
G_p	$V_{CE} = 28\text{ V}$ $P_{out} = 50\text{ W}$	$I_C = 2 \times 250\text{ mA}$	$f = 860\text{ MHz}$	7.0	8.0		dB
IMD_3	$V_{CE} = 26.5\text{ V}$ VISION = -8.0dB	$P_{out} = 25\text{ W}$ SOUND = -10 dB	$f = 860\text{ MHz}$ CHROMA = -16dB			-45	dBc

Mouser Electronics

Authorized Distributor

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